RENESAS

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GENERAL DESCRIPTION

The 844001 is a Fibre Channel Clock Generator. The 844001 uses an 18pF parallel resonant crystal over the range of 20.4MHz - 28.3MHz. For Fibre Channel applications, a 26.5625MHz crystal is used. The frequency select pin allows the device to generate either 106.25MHz or 212.5MHz from a 26.5625MHz crystal. To generate 187.5MHz for 12Gb Ethernet, a 23.4375MHz crystal is used. The 844001 uses IDT's 3^{rd} generation low phase noise VCO technology and can achieve <1ps typical rms phase jitter, easily meeting Fibre Channel and Ethernet jitter requirements. The 844001 is packaged in a small 8-pin TSSOP, making it ideal for use in systems with limited board space.

NOTE: It is not recommended to overdrive the crystal input with an external clock.

FEATURES

- One Differential LVDS output
- Crystal oscillator interface, 18pF parallel resonant crystal (20.4MHz - 28.3MHz)
- Output frequency range: 81.66MHz 226.66MHz
- VCO range: 490MHz 680MHz
- RMS phase jitter @ 106.25MHz, using a 26.5625MHz crystal (637kHz 10MHz): 0.74ps (typical)
- 3.3V or 2.5V operating supply
- 0°C to 70°C ambient operating temperature
- Available in lead-free (RoHS 6) package
- For functional replacement part use 8T49N242

COMMON CONFIGURATION TABLE - FIBRE CHANNEL, 12Gb ETHERNET

| | Inputs | | | | |
|-------------------------|----------|----|---|-----------------------------|--------|
| Crystal Frequency (MHz) | FREQ_SEL | М | Ν | Multiplication Value M/N | (MHz) |
| 26.5625 | 1 | 24 | 6 | 4 | 106.25 |
| 26.5625 | 0 | 24 | 3 | 8 | 212.5 |
| 23.4375 | 0 | 24 | 3 | 8 | 187.5 |

BLOCK DIAGRAM



PIN ASSIGNMENT



844001 8-Lead TSSOP 4.40mm x 3.0mm x 0.925mm package body G Package Top View

TABLE 1. PIN DESCRIPTIONS

| Number | Name | Ту | ре | Description |
|--------|----------------------|--------|--------|--|
| 1 | V | Power | | Analog supply pin. |
| 2 | GND | Power | | Power supply ground. |
| 3, 4 | XTAL_OUT, XTAL_IN | Input | | Crystal oscillator interface. XTAL_IN is the input, XTAL_OUT is the output. |
| 5 | FREQ_SEL | Input | Pullup | Frequency select pin. |
| 6, 7 | nQ, Q | Output | | Differential clock outputs. LVDS interface levels. |
| 8 | V | Power | | Core supply pin. |

NOTE: *Pullup* refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------|-----------------------|-----------------|---------|---------|---------|-------|
| C | Input Capacitance | | | 4 | | pF |
| R | Input Pullup Resistor | | | 51 | | kΩ |

RENESAS

ABSOLUTE **M**AXIMUM **R**ATINGS

| Supply Voltage, V_{dd} | 4.6V |
|--|---------------------------|
| Inputs, V | -0.5V to V_{_{DD}}+ 0.5 V |
| Outputs, I _o (LVDS) Continuous Current Surge Current | 10mA 15mA |
| Package Thermal Impedance, $\boldsymbol{\theta}_{_{\!$ | 101.7°C/W (0 mps) |
| Storage Temperature, T | -65°C to 150°C |

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

TABLE 3A. Power Supply DC Characteristics, $V_{dd} = V_{dda} = 3.3V \pm 5\%$, TA = 0°C to 70°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|--------|-----------------------|-----------------|------------------------|---------|-----------------|-------|
| V | Core Supply Voltage | | 3.135 | 3.3 | 3.465 | V |
| V | Analog Supply Voltage | | V _{DD} - 0.12 | 3.3 | V _{DD} | V |
| l DD | Power Supply Current | | | | 115 | mA |
| | Analog Supply Current | | | | 12 | mA |

Table 3B. Power Supply DC Characteristics, $V_{dd} = V_{dda} = 2.5V \pm 5\%$, Ta = 0°C to 70°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|---------|-----------------------|-----------------|------------------------|---------|---------|-------|
| V | Core Supply Voltage | | 2.375 | 2.5 | 2.625 | V |
| V | Analog Supply Voltage | | V _{DD} - 0.12 | 2.5 | V | V |
| | Power Supply Current | | | | 110 | mA |
| DDA | Analog Supply Current | | | | 12 | mA |

TABLE 3C. LVCMOS/LVTTL DC Characteristics, $V_{dd} = V_{dda} = 3.3V\pm5\%$ or $2.5V\pm5\%$, Ta = 0°C to 70°C to 70°

| Symbol | Parameter | | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|---------------------|----------|--|---------|---------|-----------------------|-------|
| V | | | $V_{_{DD}} = 3.3V$ | 2 | | V _{DD} + 0.3 | V |
| V IH | Input riigh voltage | | $V_{dD} = 2.5V$ | 1.7 | | V _{DD} + 0.3 | V |
| V | | | $V_{_{DD}} = 3.3V$ | -0.3 | | 0.8 | V |
| V | Input Low voltage | | V _{DD} = 2.5V | -0.3 | | 0.7 | V |
| I _{IH} | Input High Current | FREQ_SEL | $V_{_{DD}} = V_{_{IN}} = 3.465 V \text{ or } 2.625 V$ | | | 5 | μA |
| I. | Input Low Current | FREQ_SEL | $V_{_{DD}} = 3.465 V \text{ or } 2.625 V, V_{_{IN}} = 0 V$ | -150 | | | μA |

TABLE 3D. LVDS DC CHARACTERISTICS, $V_{DD} = V_{DDA} = 3.3V \pm 5\%$, TA = 0°C to 70°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|----------------------------------|-----------------|---------|---------|---------|-------|
| V _{od} | Differential Output Voltage | | 350 | 415 | 480 | mV |
| ΔV_{op} | $V_{_{OD}}$ Magnitude Change | | | | 50 | mV |
| V _{os} | Offset Voltage | | 1.225 | 1.325 | 1.425 | V |
| ΔV_{os} | V _{os} Magnitude Change | | | | 50 | mV |

NOTE: Please refer to Parameter Measurement Information for output information.

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|-----------------|----------------------------------|-----------------|---------|---------|---------|-------|
| V | Differential Output Voltage | | 300 | 390 | 480 | mV |
| ΔV_{op} | $V_{_{OD}}$ Magnitude Change | | | | 50 | mV |
| V _{os} | Offset Voltage | | 1.0 | 1.2 | 1.325 | V |
| ΔV_{os} | V _{os} Magnitude Change | | | | 50 | mV |

Table 3E. LVDS DC Characteristics, $V_{dd} = V_{dda} = 2.5V \pm 5\%$, TA = 0°C to 70°C

NOTE: Please refer to Parameter Measurement Information for output information.

TABLE 4. CRYSTAL CHARACTERISTICS

| Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|------------------------------------|-----------------|-------------|---------|---------|-------|
| Mode of Oscillation | | Fundamental | | | |
| Frequency | | 20.4 | | 28.3 | MHz |
| Equivalent Series Resistance (ESR) | | | | 50 | Ω |
| Shunt Capacitance | | | | 7 | pF |
| Drive Level | | | | 1 | mW |

NOTE: It is not recommended to overdrive the crystal input with an external clock.

Table 5A. AC Characteristics, $V_{_{DD}} = V_{_{DDA}} = 3.3V \pm 5\%$, Ta = 0°C to 70°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|---------------------------------|---------------------------------------|--|---------|---------|---------|-------|
| f _{out} | Output Frequency | | 81.66 | | 226.66 | MHz |
| | | 106.25MHz @ Integration Range: 637kHz - 10MHz | | 0.74 | | ps |
| tjit(Ø) | RMS Phase Jitter (Random); NOTE 1 | 187.5MHz @ Integration Range: 637kHz - 10MHz | | 0.48 | | ps |
| | | 212.5MHz @ Integration Range: 637kHz - 10MHz | | 0.70 | | ps |
| t _R / t _F | Output Rise/Fall Time | 20% to 80% | 175 | | 500 | ps |
| odc | | FREQ_SEL = 1 | 48 | | 52 | % |
| | | FREQ_SEL = 0 | 45 | | 55 | % |

NOTE 1: Please refer to the Phase Noise Plots following this section.

TABLE 5B. AC CHARACTERISTICS, $V_{DD} = V_{DDA} = 2.5V \pm 5\%$, TA = 0°C to 70°C

| Symbol | Parameter | Test Conditions | Minimum | Typical | Maximum | Units |
|---------------------------------|---------------------------------------|--|---------|---------|---------|-------|
| f _{out} | Output Frequency | | 81.66 | | 226.66 | MHz |
| | | 106.25MHz @ Integration Range: 637kHz - 10MHz | | 0.97 | | ps |
| tjit(Ø) | RMS Phase Jitter (Random); NOTE 1 | 187.5MHz @ Integration Range: 637kHz - 10MHz | | 0.58 | | ps |
| | | 212.5MHz @ Integration Range: 637kHz - 10MHz | | 0.95 | | ps |
| t _R / t _F | Output Rise/Fall Time | 20% to 80% | 175 | | 500 | ps |
| odc | Output Duty Cycle | FREQ_SEL = 1 | 48 | | 52 | % |
| | Output Duty Cycle | FREQ_SEL = 0 | 45 | | 55 | % |

NOTE 1: Please refer to the Phase Noise Plots following this section.



OFFSET FREQUENCY (Hz)



OFFSET FREQUENCY (Hz)

PARAMETER MEASUREMENT INFORMATION



APPLICATION INFORMATION

Power Supply Filtering Techniques

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. The 844001 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. $V_{_{DD}}$ and $V_{_{DDA}}$ should be individually connected to the power supply plane through vias, and bypass capacitors should be used for each pin. To achieve optimum jitter performance, power supply isolation is required. *Figure 1* illustrates how a 10 Ω resistor along with a 10 μ F and a .01 μ F bypass capacitor should be connected to each $V_{_{DDA}}$ pin.



FIGURE 1. POWER SUPPLY FILTERING

CRYSTAL INPUT INTERFACE

The 844001 has been characterized with 18pF parallel resonant crystals. The capacitor values, C1 and C2, shown in *Figure 2* below were determined using a 26.5625MHz, 18pF

parallel resonant crystal and were chosen to minimize the ppm error. The optimum C1 and C2 values can be slightly adjusted for different board layouts.



Figure 2. CRYSTAL INPUT INTERFACE

3.3V, 2.5V LVDS DRIVER TERMINATION

A general LVDS interface is shown in *Figure 4.* In a 100Ω differential transmission line environment, LVDS drivers require a matched load termination of 100Ω across near

the receiver input. For a multiple LVDS outputs buffer, if only partial outputs are used, it is recommended to terminate the unused outputs.



FIGURE 4. TYPICAL LVDS DRIVER TERMINATION

Power Considerations

This section provides information on power dissipation and junction temperature for the 844001. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 844001 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{no} = 3.3V + 5\% = 3.465V$, which gives worst case results.

Power (core)_{MAX} = V_{DD MAX} * (I_{DD MAX} + I_{DDA MAX}) = 3.465V * (115mA + 12mA) = 440mW

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C.

The equation for Tj is as follows: $Tj = \theta_{JA} * Pd_total + T_A$

Tj = Junction Temperature

 θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

 $T_{A} = Ambient Temperature$

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{A} must be used. Assuming a moderate air flow of 1 meter per second and a multi-layer board, the appropriate value is 90.5°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 70°C with all outputs switching is: $70^{\circ}C + 0.440W *90.5^{\circ}C/W = 109.8^{\circ}C$. This is well below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

TABLE 6. THERMAL RESISTANCE θ_{JA} FOR 8-PIN TSSOP, FORCED CONVECTION

| θ_{JA} by Velocity (Meters per Second) | | | | | |
|---|-----------------------|----------------------|------------------------|--|--|
| Multi-Layer PCB, JEDEC Standard Test Boards | 0 101.7°C/W | 1 90.5°C/W | 2.5 89.8°C/W | | |

RELIABILITY INFORMATION

TABLE 7. $\boldsymbol{\theta}_{_{JA}} \text{vs.}$ Air Flow Table for 8 Lead TSSOP

| θ_{JA} by Velocity (Meters per Second) | | | | |
|---|-----------------------|----------------------|------------------------|--|
| Multi-Layer PCB, JEDEC Standard Test Boards | 0 101.7°C/W | 1 90.5°C/W | 2.5 89.8°C/W | |
| NOTE: An airflow of 1 meter per second is strongly recommended. | | | | |

TRANSISTOR COUNT

The transistor count for 844001 is: 2533

PACKAGE OUTLINE - G SUFFIX FOR 8 LEAD TSSOP



TABLE 8. PACKAGE DIMENSIONS

| CYMDOL | Millimeters | | |
|--------|-------------|---------|--|
| SYMBOL | Minimum | Maximum | |
| N | 8 | | |
| А | | 1.20 | |
| A1 | 0.05 | 0.15 | |
| A2 | 0.80 | 1.05 | |
| b | 0.19 | 0.30 | |
| С | 0.09 | 0.20 | |
| D | 2.90 | 3.10 | |
| E | 6.40 BASIC | | |
| E1 | 4.30 | 4.50 | |
| е | 0.65 BASIC | | |
| L | 0.45 | 0.75 | |
| α | 0° | 8° | |
| aaa | | 0.10 | |

Reference Document: JEDEC Publication 95, MO-153

TABLE 9. ORDERING INFORMATION

| Part/Order Number | Marking | Package | Shipping Packaging | Temperature |
|-------------------|---------|--------------------------|--------------------|-------------|
| 844001AGLF | 001AL | 8 lead "Lead-Free" TSSOP | tube | 0°C to 70°C |
| 844001AGLFT | 001AL | 8 lead "Lead-Free" TSSOP | tape & reel | 0°C to 70°C |

| REVISION HISTORY SHEET | | | | |
|------------------------|----------|-------------------|---|---------|
| Rev | Table | Page | Description of Change | Date |
| A | T4 T9 | 1 4 8 12 | Deleted HiPerClockS references. Crystal Characteristics Table - added note. Deleted application note, LVCMOS to XTAL Interface. Deleted quantity from tape and reel. | 9/23/12 |
| А | Т9 | 12 | Ordering Information - Removed leaded devices. Updated datasheet header and footer. | 12/8/15 |
| A | | | Product Discontinuation Notice - Last time buy expires May 6, 2017. PDN CQ-16-01 | 6/2/16 |



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